SFP(B)100N80

N-MOSFET 80V, 100A, 5.7mΩ

Features

- Adanced trench process technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g x R_{DS(on)}$ product(FOM)
- Fast Switching
- High Ruggedness

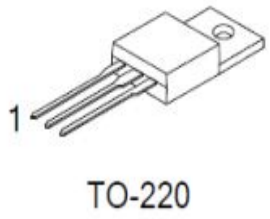
Product Summary

VDS	80V
$R_{DS(on)@VGS=10V}$	5.7 mΩ
I_D	100A

Application

- Motor Drives
- UPS (Uninterruptible Power Supplies)
- DC/DC converter
- General purpose applications

Part ID	Package Type	Marking
SFP120N80	TO-220	100N80
SFB120N80	TO-263	100N80



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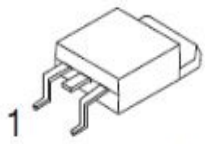

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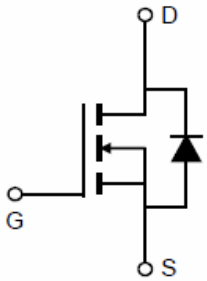


Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	80	V
Continuous drain current T_C = 25°C T_C = 100°C	I_D	100 80	A
Pulsed drain current T_C = 25°C, t_p limited by T_{jmax}	$I_{D\ pulse}$	480	
Avalanche energy, single pulse (L=1mH,Rg=25Ω, ID=sweep(14A~46A))	E_{AS}	1000	mJ
Gate-emitter voltage	V_{GS}	±25	V
Power dissipation T_C = 25°C	P_{tot}	178	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	℃

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.66	℃/W
Thermal resistance, junction – ambient. Max	R_{thJA}	62.0	

Electrical Characteristic, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250uA	80	85	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA T_j=25°C T_j=125°C	2.0 -	3.0	4.0 -	
Zero gate voltage drain current	I_{DSS}	V_{DS}=64V,V_{GS}=0V T_j=25°C T_j=125°C	- -	0.05 -	1 5	μA
Gate-source leakage current	I_{GSS}	V_{GS}=20V,V_{DS}=0V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=40A, T_j=25°C	-	5.6	7.0	mΩ
Dynamic Characteristic						
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=40V, f=1MHz	-	3240	-	pF
Output Capacitance	C_{oss}		-	1200	-	
Reverse Transfer Capacitance	C_{rss}		-	28.0	-	
Gate Total Charge	Q_G	V_{GS}=10V, V_{DS}=40V, I_D=50A, f=1MHz	-	59.0	-	nC
Gate-Source charge	Q_{gs}		-	13.0	-	
Gate-Drain charge	Q_{gd}		-	11.0	-	
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{GS}=10V, V_{DS}=40V, R_L=3Ω	-	23.2	-	ns
Rise time	t_r		-	42.4	-	
Turn-off delay time	$t_{d(off)}$		-	48.6	-	
Fall time	t_f		-	25.7	-	
Gate resistance	R_G	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	1.7	-	Ω
Body Diode Characteristic						
Body Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_{SD}=30A	-	0.80	1.3	V
Body Diode Reverse Recovery Time	t_{rr}	I_F=20A, dI/dt=500A/μs		63		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=20A, dI/dt=500A/μs		630		nC

Figure 1. Gate-Charge Characteristics

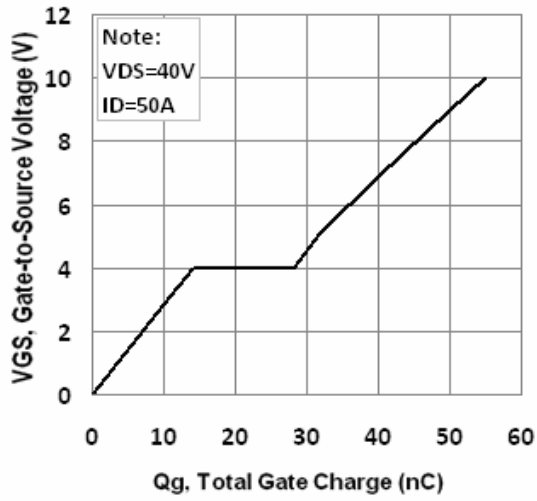


Figure 2. Capacitance Characteristics

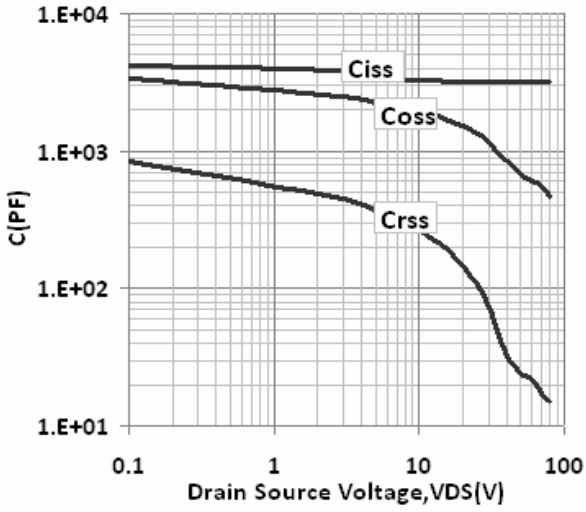


Figure 9: Normalized Maximum Transient Thermal Impedance (R_{thJC})

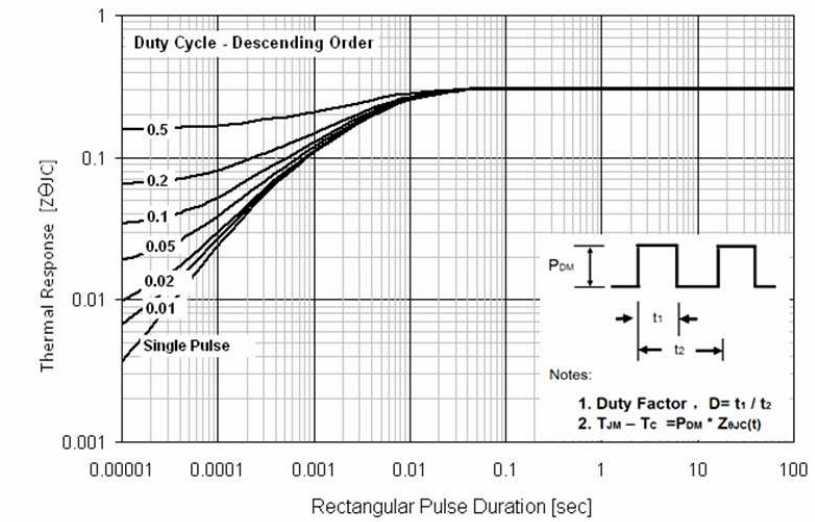
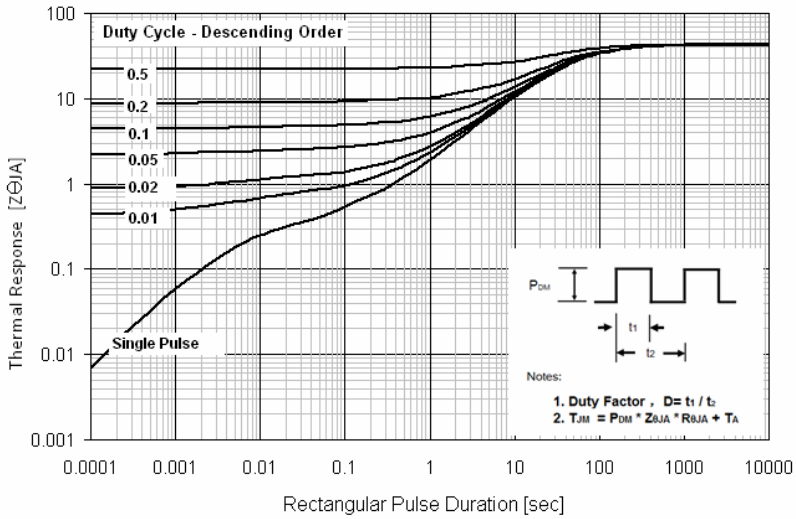
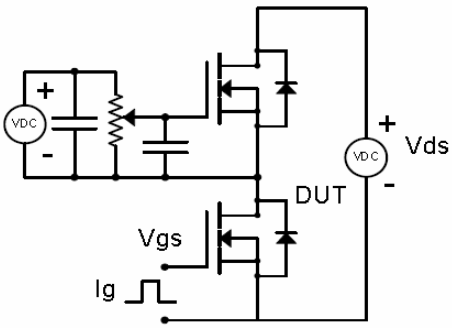


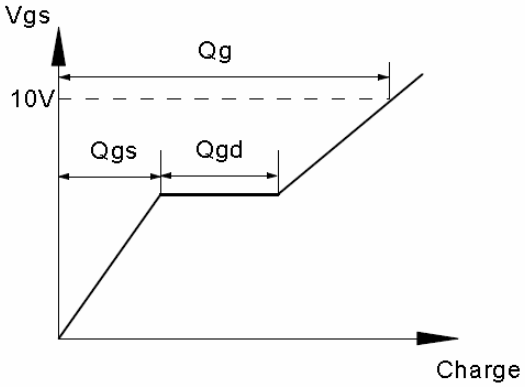
Figure 3: Normalized Maximum Transient Thermal Imp edance (R_{thJA})



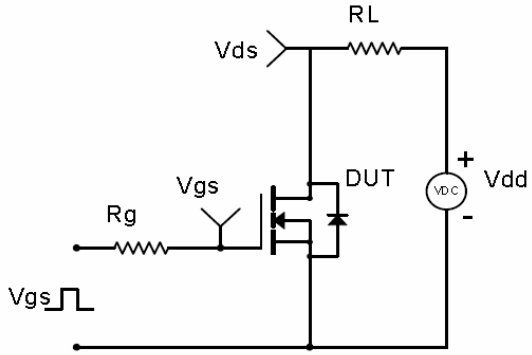
Test Circuit & Waveform

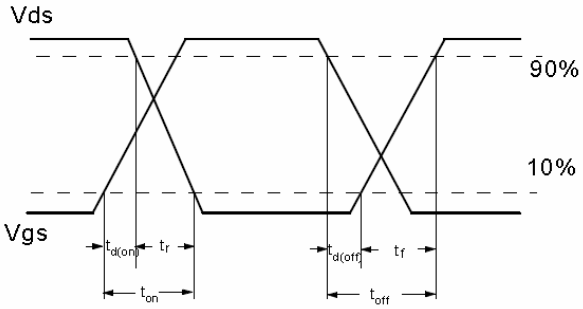
Gate Charge Test Circuit & Waveform



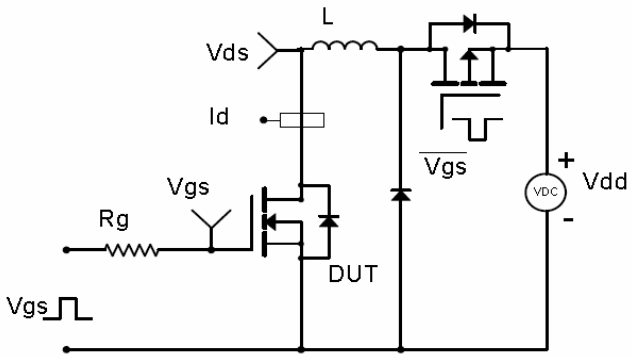


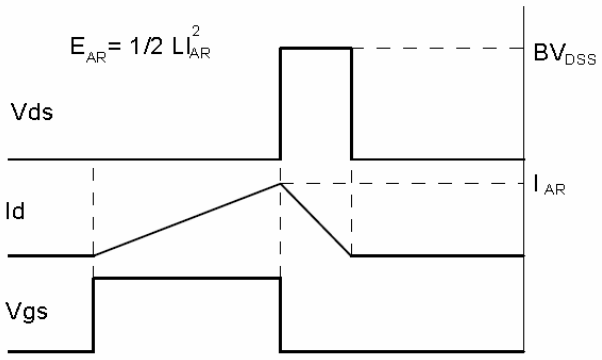
Resistive Switching Test Circuit & Waveforms



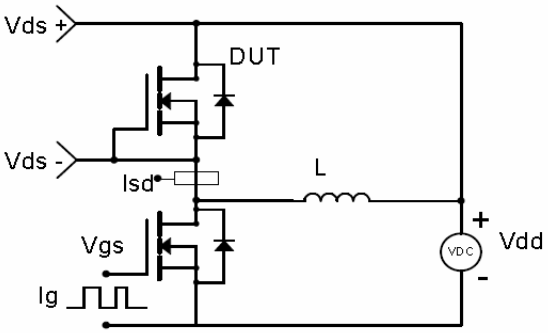


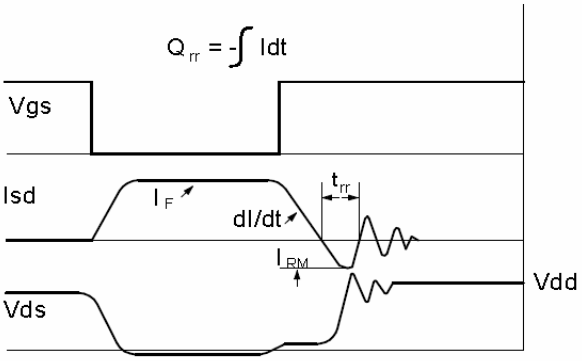
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms





PACKAGE DIMENSION

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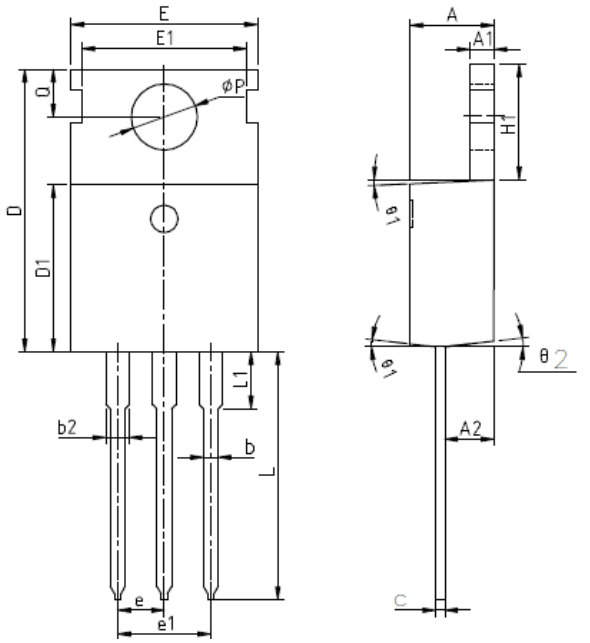

SYMBOL	MIN	NOM	MAX
A	4.27	4.57	4.87
A1	1.15	1.30	1.45
A2	2.10	2.40	2.70
b	0.70	0.80	1.00
b2	1.17	1.27	1.50
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.70	6.70	7.00
E	9.70	10.00	10.30
E1	-	8.70	-
E2	9.65	10.00	10.35
E3	7.00	8.00	8.40
e		2.54 BSC	
e1		5.08 BSC	
H1	6.00	6.50	6.85
L	12.75	13.50	13.90
L1	-	3.10	3.40
ΦP	3.45	3.60	3.75
Q	2.60	2.80	3.00
θ1	4°	7°	10°
θ2	0°	3°	6°

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